

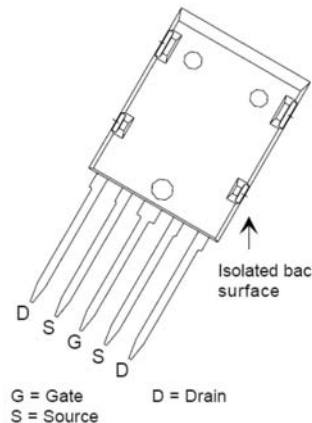
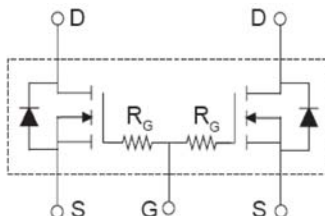
# Trench™ Power MOSFET Common-Gate Pair

## IXTL2x180N10T

$$\begin{aligned} V_{DSS} &= 100V \\ I_{D25} &= 2 \times 100A \\ R_{DS(on)} &\leq 9m\Omega \end{aligned}$$

(Electrically Isolated Back Surface)

N-Channel Enhancement Mode  
Avalanche Rated  
Fast Intrinsic Rectifier



| Symbol       | Test Conditions  | Maximum Ratings  |                  |
|--------------|--|------------------|------------------|
| $V_{DSS}$    | $T_J = 25^\circ\text{C}$ to $175^\circ\text{C}$                          | 100              | V                |
| $V_{DGR}$    | $T_J = 25^\circ\text{C}$ to $175^\circ\text{C}$ , $R_{GS} = 1M\Omega$    | 100              | V                |
| $V_{GSS}$    | Continuous   | $\pm 20$         | V                |
| $V_{GSM}$    | Transient  | $\pm 30$         | V                |
| $I_{D25}$    | $T_C = 25^\circ\text{C}$   | 100              | A                |
| $I_{L(RMS)}$ | External Lead Current Limit  | 75               | A                |
| $I_{DM}$     | $T_C = 25^\circ\text{C}$ , Pulse Width Limited by $T_{JM}$               | 450              | A                |
| $I_A$        | $T_C = 25^\circ\text{C}$   | 25               | A                |
| $E_{AS}$     | $T_C = 25^\circ\text{C}$   | 750              | mJ               |
| $P_D$        | $T_C = 25^\circ\text{C}$   | 150              | W                |
| $dv/dt$      | $I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 175^\circ\text{C}$ | 3                | V/ns             |
| $T_J$        |  | $-55 \dots +175$ | $^\circ\text{C}$ |
| $T_{JM}$     |  | 175              | $^\circ\text{C}$ |
| $T_{stg}$    |  | $-55 \dots +175$ | $^\circ\text{C}$ |
| $T_L$        | 1.6mm (0.062 in.) from Case for 10s                                      | 300              | $^\circ\text{C}$ |
| $T_{SOLD}$   | Plastic Body for 10s   | 260              | $^\circ\text{C}$ |
| $F_C$        | Mounting Force   | 20..120 / 9..27  | N/lb.            |
| Weight       |  | 8                | g                |

### Features

- Silicon Chip on Direct-Copper Bond (DCB) Substrate
- Isolated Mounting Surface
- 2500V~ Electrical Isolation
- 175°C Operating Temperature
- Avalanche Rated
- High Current Handling Capability
- Fast Intrinsic Rectifier
- Low  $R_{DS(on)}$  and  $Q_G$

### Advantages

- High Power Density
- Easy to Mount
- Space Savings

### Applications

- Automotive
  - Motor Drives
  - DC/DC Conversion
  - 42V Power Bus
  - ABS Systems
- DC/DC Converters and Off-Line UPS
- Primary Switch for 24V and 48V Systems
- High Current Switching Applications
- Distributed Power Architectures and VRMs
- Electronic Valve Train Systems
- High Voltage Synchronous Rectifier

| Symbol       | Test Conditions<br>( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified) | Characteristic Values |      |                          |
|--------------|---|-----------------------|------|--------------------------|
|              |   | Min.                  | Typ. | Max.                     |
| $BV_{DSS}$   | $V_{GS} = 0V$ , $I_D = 250\mu A$  | 100                   |      | V                        |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$ , $I_D = 250\mu A$                                      | 2.5                   |      | 4.5 V                    |
| $I_{GSS}$    | $V_{GS} = \pm 20V$ , $V_{DS} = 0V$  |                       |      | $\pm 200$ nA             |
| $I_{DSS}$    | $V_{DS} = V_{DSS}$ , $V_{GS} = 0V$<br>$T_J = 150^\circ\text{C}$           |                       |      | 5 $\mu A$<br>250 $\mu A$ |
| $R_{DS(on)}$ | $V_{GS} = 10V$ , $I_D = 50A$ , Note 1                                     |                       |      | 9 m $\Omega$             |

| Symbol       | Test Conditions<br>( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)   | Characteristic Values |      |                       |
|--------------|---|-----------------------|------|-----------------------|
|              |   | Min.                  | Typ. | Max.                  |
| $g_{fs}$     | $V_{DS} = 10\text{V}$ , $I_D = 60\text{A}$ , Note 1   | 70                    | 110  | S                     |
| $C_{iss}$    | $V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$  |                       | 6900 | pF                    |
| $C_{oss}$    |   |                       | 923  | pF                    |
| $C_{rss}$    |   |                       | 162  | pF                    |
| $R_{Gi}$     | Gate Input Resistance   |                       | 3.0  | $\Omega$              |
| $t_{d(on)}$  | <b>Resistive Switching Times</b><br>$V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 25\text{A}$<br>$R_G = 3.3\Omega$ (External) |                       | 33   | ns                    |
| $t_r$        |   |                       | 54   | ns                    |
| $t_{d(off)}$ |   |                       | 42   | ns                    |
| $t_f$        |   |                       | 31   | ns                    |
| $Q_{g(on)}$  | $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 25\text{A}$   |                       | 151  | nC                    |
| $Q_{gs}$     |   |                       | 39   | nC                    |
| $Q_{gd}$     |   |                       | 45   | nC                    |
| $R_{thJC}$   |   | 0.15                  |      | $1.0^\circ\text{C/W}$ |
| $R_{thCS}$   |   |                       |      | $^\circ\text{C/W}$    |

## Source-Drain Diode

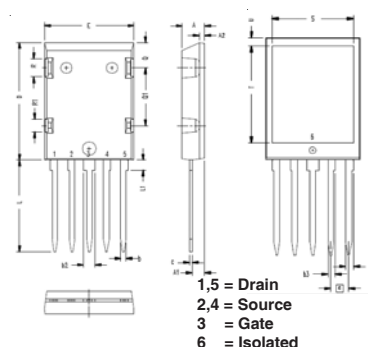
| Symbol   | Test Conditions<br>( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)                          | Characteristic Values |      |       |
|----------|--|-----------------------|------|-------|
|          |  | Min.                  | Typ. | Max.  |
| $I_s$    | $V_{GS} = 0\text{V}$   |                       |      | 180 A |
| $I_{SM}$ | Repetitive, Pulse Width Limited by $T_{JM}$  |                       |      | 450 A |
| $V_{SD}$ | $I_F = 50\text{A}$ , $V_{GS} = 0\text{V}$ , Note 1   |                       |      | 1.0 V |
| $t_{rr}$ | $I_F = 25\text{A}$ , $V_{GS} = 0\text{V}$<br>$-di/dt = 100\text{A}/\mu\text{s}$ , $V_R = 50\text{V}$ |                       | 60   | ns    |

Note 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

## PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

## ISOPLUS I5-Pak™ (IXTL) Outline



| SYM | INCHES   |       | MILLIMETERS |       |
|-----|----------|-------|-------------|-------|
|     | MIN      | MAX   | MIN         | MAX   |
| A   | .190     | .205  | 4.83        | 5.21  |
| A1  | .102     | .118  | 2.59        | 3.00  |
| A2  | .046     | .055  | 1.17        | 1.40  |
| b   | .045     | .055  | 1.14        | 1.40  |
| b1  | .063     | .072  | 1.60        | 1.83  |
| b2  | .100     | .110  | 2.54        | 2.79  |
| b3  | .058     | .068  | 1.47        | 1.73  |
| c   | .020     | .029  | 0.51        | 0.74  |
| D   | 1.020    | 1.040 | 25.91       | 26.42 |
| E   | .770     | .799  | 19.56       | 20.29 |
| e   | .150 BSC |       | 3.81 BSC    |       |
| L   | .780     | .820  | 19.81       | 20.83 |
| L1  | .080     | .102  | 2.03        | 2.59  |
| Q   | .210     | .235  | 5.33        | 5.97  |
| Q1  | .490     | .513  | 12.45       | 13.03 |
| R   | .150     | .180  | 3.81        | 4.57  |
| R1  | .100     | .130  | 2.54        | 3.30  |
| S   | .668     | .690  | 16.97       | 17.53 |
| T   | .801     | .821  | 20.34       | 20.85 |
| U   | .085     | .080  | 1.85        | 2.03  |

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

|           |           |           |           |              |              |              |              |              |             |
|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|-------------|
| 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665    | 6,404,065 B1 | 6,683,344    | 6,727,585    | 7,005,734 B2 | 7,157,338B2 |
| 4,860,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343    | 6,710,405 B2 | 6,759,692    | 7,063,975 B2 |             |
| 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505    | 6,710,463    | 6,771,478 B2 | 7,071,537    |             |



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